

ABSTRACT OF THE DISCLOSURE

[0086] A silicon-on-insulator (SOI) electrostatic discharge (ESD) protection device that can protect very sensitive thin gate oxides by limiting the power dissipation during the ESD event, which is best achieved by reducing the voltage drop across the active (protection) device during an ESD event. In one embodiment, the invention provides very low triggering and holding voltages. Furthermore, the SOI protection device of the present invention has low impedance and low power dissipation characteristics that reduce voltage build-up, and accordingly, enable designers to fabricate more area efficient protection device